

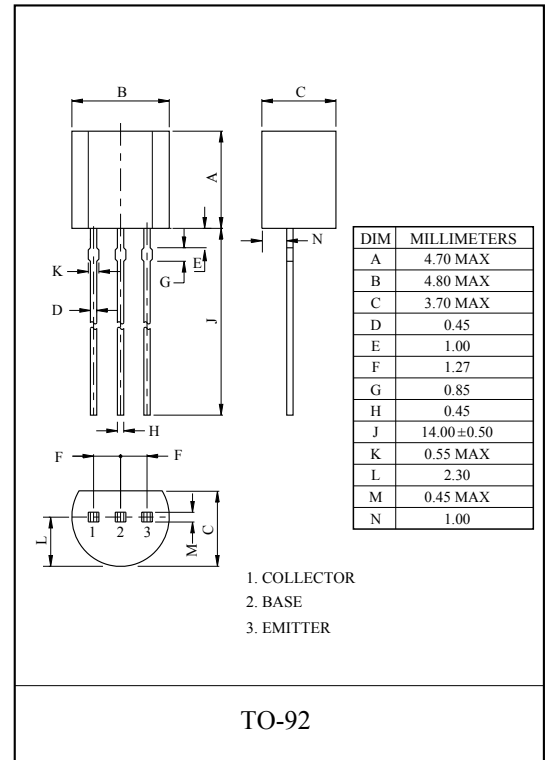
LOW NOISE APPLICATION.

FEATURE

- For Complementary with NPN Type BC549/550.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	BC559	-30	V
	BC560	-50	
Collector-Emitter Voltage	BC559	-30	V
	BC560	-45	
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA
Collector Power Dissipation	P _C	625	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	BC559	I _C =-10mA, I _B =0	-30	-	-	V
	BC560		-45	-	-	
Collector-Base Breakdown Voltage	BC559	I _C =-10μA, I _E =0	-30	-	-	V
	BC560		-50	-	-	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5.0	-	-	V
Collector Cut-off Current	I _{CB0}	V _{CB} =-30V, I _E =0	-	-	-15	nA
DC Current Gain	h _{FE}	I _C =-2mA, V _{CE} =-5V	110	-	800	
Base-Emitter Voltage	V _{BE(ON)}	I _C =-2mA, V _{CE} =-5V	-0.55	-	-0.7	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B =-5mA	-	-	-0.6	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-100mA, I _B =-5mA	-	-0.9	-	V
Transition Frequency	f _T	I _C =-10mA, V _{CE} =-5V, f=100MHz	-	300	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	-	7.0	pF
Noise Figure	NF	I _C =-200μA, V _{CE} =-5V R _g =10kΩ, f=1kHz	-	-	4.0	dB

Note : h_{FE} Classification A:110~220, B:200~450, C:420~800